High Performance InGaAs p-i-n Photodiode

'FC' Active Device Mount

13PD300-FC

The 13PD300-FC, an InGaAs photodiode with a 300µm-diameter photosensitive region packaged in a TO-46 header and aligned in an FC active device mount, is designed for applications in both moderate-bit-rate fiberoptic communications and high sensitivity measurement equipment. This device is one of the most versatile of the Telcom Devices' family of optoelectronic components. Planar semiconductor design and dielectric passivation provide superior performance. Reliability is assured by hermetic sealing and a 100% purge burn-in (200°C, 15 hours, V_r = 20V).

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics:

Parameters	Test Conditions	Min	Typ	Max	Units
Operating Voltage	-	-	-	-20	Volts
Dark Current	-5V	-	1.0	10	nA
Capacitance	-5V	-	4	12	pF
Responsivity	1300nm	0.7	0.9	-	A/W
Rise/Fall	-	-	-	0.5	ns
Frequency Response	(-3dB)	-	300	-	MHz

Absolute Maximum Ratings

Reverse Voltage	30 Volts
Forward Current	25 mA
Reverse Current	5 mA
Operating Temperature	-40°C to + 85°C
Storage Temperature	-40°C to + 85°C
Soldering Temperature	250°C

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